



Bipolar PNP Bare Die – BTP6446

Part Description

The BTP6446 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN6444

Key Parameters:

- VCBO = -50V
- VCEO = -50V
- VEBO = -5V
- hFE = 63-555 @ VCE = -6V, IC = -0.001A
- VCE(Sat) = -0.3V @ IC = -0.1A, IB = -10mA
- fT = 140 MHz @ VCE = -12V, IE = 0A
- COBO = 5pF @ VCB = -12V

Features

Low VCE(sat). Designed to provide performance equivalent to ROHM 2SA1037

Die Size (Unawn)

350µm X 350µm, 14 Mils X 14 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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